### MCH6341

# Power MOSFET -30V, 59mΩ, -5A, Single P-Channel



http://onsemi.com

#### **Features**

- · Low RDS(on)
- · Pb-free and RoHS Compliance

- · 4V drive
- · ESD diode-Protected gate

#### **Specifications**

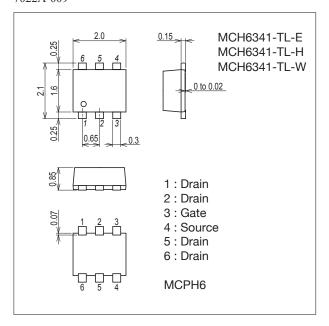
#### **Absolute Maximum Ratings** at Ta=25°C

| Parameter               | Symbol | Conditions   | Ratings     | Unit |
|-------------------------|--------|--|-------------|------|
| Drain-to-Source Voltage | VDSS   |  | -30         | V    |
| Gate-to-Source Voltage  | VGSS   |  | ±20         | V    |
| Drain Current (DC)      | ID     |  | -5          | А    |
| Drain Current (Pulse)   | IDP    | PW≤10μs, duty cycle≤1%   | -20         | А    |
| Power Dissipation       | PD     | When mounted on ceramic substrate (1200mm <sup>2</sup> ×0.8mm) | 1.5         | W    |
| Junction Temperature    | Tj     |  | 150         | °C   |
| Storage Temperature     | Tstg   |  | -55 to +150 | °C   |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **Package Dimensions**

unit : mm (typ) 7022A-009



#### **Product & Package Information**

• Package : MCPH6

• JEITA, JEDEC : SC-88, SC-70-6, SOT-363

• Minimum Packing Quantity : 3,000 pcs./reel

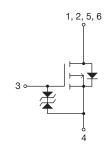
#### Packing Type: TL

## TL

#### Marking



#### **Electrical Connection**



#### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

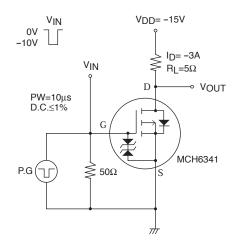
#### MCH6341

#### **Electrical Characteristics** at Ta=25°C

| Parameter                                  | Symbol                | Conditions  | Ratings         |       |      | Unit |
|--|-----------------------|---|-----------------|-------|------|------|
|  |                       | Conditions  | min             | typ   | max  | Unit |
| Drain-to-Source Breakdown Voltage          | V(BR)DSS              | I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V                         | -30             |       |      | V    |
| Zero-Gate Voltage Drain Current            | IDSS                  | V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V                        |                 |       | -1   | μΑ   |
| Gate-to-Source Leakage Current             | IGSS                  | V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V                        |                 |       | ±10  | μΑ   |
| Gate Threshold Voltage                     | V <sub>GS</sub> (th)  | V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA -1.2                  |                 |       | -2.6 | V    |
| Forward Transconductance                   | 9FS                   | V <sub>DS</sub> =-10V, I <sub>D</sub> =-3A                        | 2.8             | 4.8   |      | S    |
| Static Drain-to-Source On-State Resistance | RDS(on)1              | I <sub>D</sub> =-3A, V <sub>G</sub> S=-10V                        | D=-3A, VGS=-10V |       | 59   | mΩ   |
|  | R <sub>DS</sub> (on)2 | I <sub>D</sub> =-1.5A, V <sub>G</sub> S=-4.5V                     |                 | 71    | 100  | mΩ   |
|  | R <sub>DS</sub> (on)3 | I <sub>D</sub> =-1.5A, V <sub>G</sub> S=-4V                       |                 | 82    | 115  | mΩ   |
| Input Capacitance                          | Ciss                  |   |                 | 430   |      | pF   |
| Output Capacitance                         | Coss                  | VDS=-10V, f=1MHz  |                 | 105   |      | pF   |
| Reverse Transfer Capacitance               | Crss                  | ]   |                 | 75    |      | pF   |
| Turn-ON Delay Time                         | t <sub>d</sub> (on)   |   |                 | 7.5   |      | ns   |
| Rise Time                                  | t <sub>r</sub>        | Occupation of Track Councils                                      |                 | 26    |      | ns   |
| Turn-OFF Delay Time                        | t <sub>d</sub> (off)  | See specified Test Circuit.                                       |                 | 45    |      | ns   |
| Fall Time                                  | tf                    | ]   |                 | 35    |      | ns   |
| Total Gate Charge                          | Qg                    |   |                 | 10    |      | nC   |
| Gate-to-Source Charge                      | Qgs                   | V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-5A |                 | 2.0   |      | nC   |
| Gate-to-Drain "Miller" Charge              | Qgd                   | 1   |                 | 2.5   |      | nC   |
| Forward Diode Voltage                      | V <sub>SD</sub>       | I <sub>S</sub> =-5A, V <sub>GS</sub> =0V                          |                 | -0.87 | -1.5 | V    |

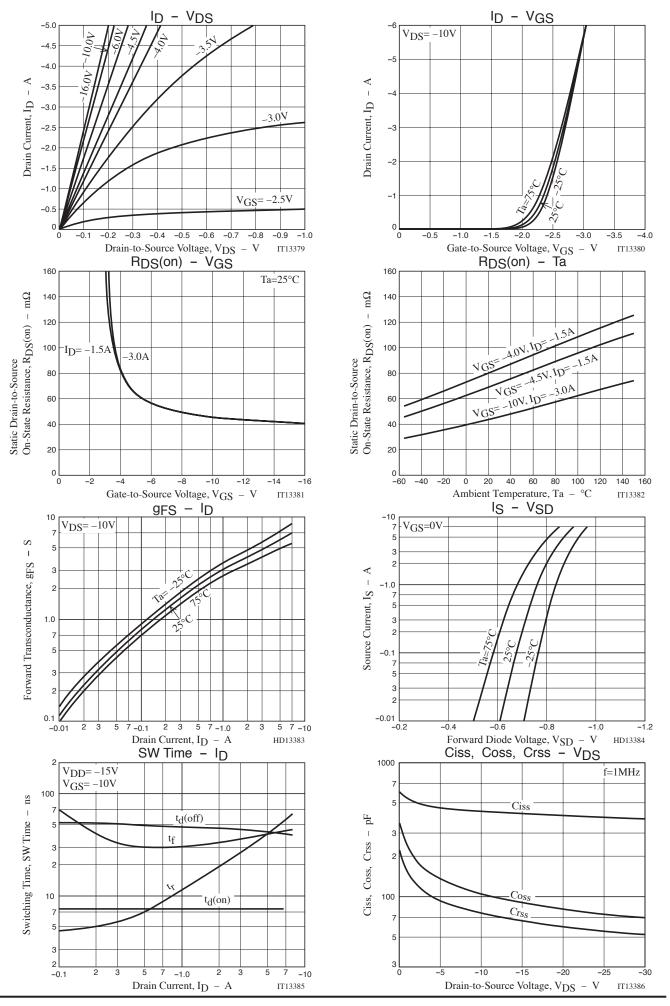
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **Switching Time Test Circuit**

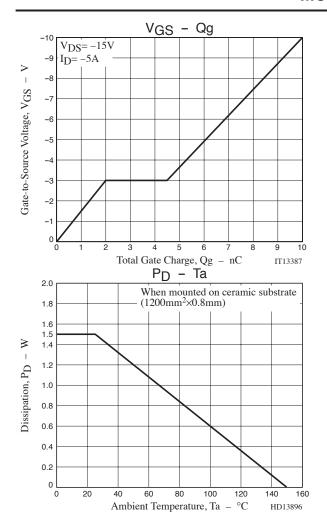


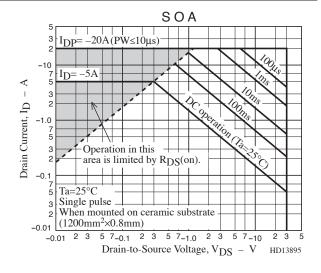
#### **Ordering Information**

| Device       | Package | Shipping       | memo                     |  |
|--------------|---------|----------------|--------------------------|--|
| MCH6341-TL-E | МСРН6   | 3,000pcs./reel | Pb Free                  |  |
| MCH6341-TL-H | MCPH6   | 3,000pcs./reel | Pb Free and Halogen Free |  |
| MCH6341-TL-W | MCPH6   | 3,000pcs./reel | Pb Free and Halogen Free |  |



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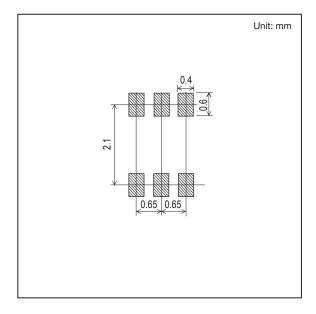


#### **Outline Drawing**

MCH6341-TL-E, MCH6341-TL-H, MCH6341-TL-W

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#### **Land Pattern Example**



Note on usage: Since the MCH6341 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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